

Monday 07th Oct	Lecture/ Invited Talk	Topic/Speaker
08:00 – 09:20	Registration	
09:20 – 09:30	Prof. Sven Hofling	Welcome and opening remarks
09:30 – 10:00	Prof. Wegscheider (ETH-Zurich)	Highest-mobility arsenide and antimony-based heterostructures
10:00 – 10:15	Sebastian Schmid (JMU Würzburg)	Topological insulators based on TQW structures
10:15 – 10:45(a)	Coffee break/registration	Wafer Technology, nextnano
10:45 – 11:00	Dr. Robert Weih (nanoplus)	Inter-band Cascade lasers grown by molecular beam epitaxy
11:00 – 11:15	Maximilian Beiser (TU Wien)	Frequency comb generation based on Inter-band Cascade lasers
11:15 – 11:30	Miriam Giparakis (TU Wein)	Selective Emission of a THz QCL using a Magnetic Field
11:30 – 11:45	Philipp Gribisch (Institut für Materialien und Bauelemente der Elektronik Leibniz Universität Hannover)	Investigations on novel crystal structures in Gd ₂ O ₃ thin films grown on Si(001)
12:00 – 14:00	Lunch/registration (MSL)	Riber, Episerve, DCA
14:00 – 14:30	Prof. Brunner (JMU Würzburg)	Topological Insulator Materials: MBE, structural and electronic properties
14:30 – 15:15	Dr. Peter Schüffelgen (Forschungszentrum Jülich)	Selective area growth and stencil lithography for topological quantum devices
14:45 – 15:00	Dr. Gregor Mussler (Forschungszentrum Jülich)	MBE growth of dual topological insulator Bi ₁ Te ₁ and 2D topological insulator Bi ₄ Te ₃
15:00 – 15:15	Micheal Schleenvoigt(Forschungszentrum Jülich GmbH)	UHV Lithography for STM Investigations of 3D Topological Insulators-Superconductor Hybrid Arrays
15:15 – 15:45	Coffee break	Scienta Omicron GmbH, abcr GmbH
15:45 – 16:00	Dr. Arne Ludwig (Ruhr-Universität Bochum)	Epitaxial alignment of quantum dots
16:00 – 16:15	Dr. Wolfgang Braun (Max-Planck-Institut für Festkörperforschung)	Thermal Laser Epitaxy
16:15 – 16:30	Tanja Finke (Institut für Nanostrukturtechnologie und Analytik, Kassel)	GaAs based quantum dot structures for VECSEL and MIXSEL applications
16:00 – 16:45	Dr. Christian Schneider(JMU Wuerzburg)	Growth and Technology aspects in the implementation of GaAs-based Semiconductor Single Photon Sources
16:45 – 18:45	Poster session, lab tour (MSL)	
19:00 –	Workshop dinner(Juliussspital)	

Program-Tuesday

Tuesday 08th Oct	Lecture/ Invited Talk	Topic/Speaker
09:00 – 09:30	Prof. Böhm (TUM)	InP- and GaSb-based VCSELs suitable for gas-sensing experiments in the wavelength range 2-4 μm
09:30 – 09:45	Yvo Barnscheidt (Institut für Materialien und Bauelemente der Elektronik Leibniz Universität Hannover)	Filtering Threading-Dislocations in Ge/Si Heteroepitaxy by the Introduction of Carbon Delta Layers
09:45 – 10:00	Dr. Alexander Pawlis (Peter Grünberg Institut PGI-9, Forschungszentrum Jülich GmbH)	MBE Growth and Optical Properties of Isotopically Purified ZnSe Heterostructures
10:00 – 10:15	Dr. Martin Heilmann (Paul-Drude-Institut, Berlin)	Substrate-related influences on van der Waals epitaxy of hexagonal boron nitride on graphene
10:15 – 10:45	Coffee break	RTA Instruments Ltd, VBL Sprl
10:45 – 11:00	Dr. Piero Mazzolini (Paul-Drude-Institut, Berlin)	Molecular Beam Epitaxy of (010) β -Ga ₂ O ₃ Homoepitaxial Thin Films
11:00 – 11:15	Pujitha Perla (Peter Grünberg Institut PGI-9, Forschungszentrum Jülich GmbH)	Fabrication of In-situ Josephson contacts on InAs nanowires
11:15 – 11:30	Dr. Stephan Farrel (Veeco Inc.)	Development of a High-Purity, High-Concentration Ozone Delivery System and Safety Considerations for MBE Growth of Oxide Materials
11:30 – 11:45	Wenische (AIM Infrarot-Module GmbH)	MBE Technology at AIM
11:45 – 12:00	Prof. Sven Höfling	Closing remarks, next DEMBE announcement
12:00 – 14:00	Lunch, lab visits (MSL), and departure	VEECO, STAIB INSTRUMENTS GmbH, MBE Komponenten